



RECEIVED

DEC 30 2002

TECHNOLOGY CENTER 2800

#11/Amend  
1.7.0.318  
C. Moore  
ATTENTION: BOX AFTER FINAL  
RESPONSE UNDER 37 C.F.R. § 1.116  
EXPEDITED PROCEDURE REQUESTED  
EXAMINING GROUP 2814

PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.2613

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Katsuhiko HIEDA ) Group Art Unit: T. Le  
)  
Application No.: 09/916,509 ) Examiner: 2814  
)  
Filed: July 30, 2001 )  
)  
For: FIELD EFFECT TRANSISTOR )  
USING SIDE-WALL GATES TO )  
PREVENT PUNCH-THROUGH )  
(As Amended) )

Commissioner for Patents  
Washington, DC 20231

Sir:

**AMENDMENT AFTER FINAL**

In reply to the Final Office Action dated October 24, 2002, the period for  
response to which extends through January 24, 2003, please amend the application as  
follows:

**IN THE CLAIMS:**

Please amend claims 1 and 2 as follows:

1. (Twice Amended) A semiconductor device comprising:  
a convex semiconductor layer provided on a semiconductor substrate;

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNN LLP

1300 I Street, NW  
Washington, DC 20006  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com

Please  
DO NOT Enter  
T.L.  
01/08/02